UNITED STATES PATENT AND TRADEMARK OFFICE

CERTIFICATE OF CORRECTION

PATENT NO. : 7,037,862 B2
APPLICATION NO. : 09/881408
DATED : May 2, 2006
INVENTOR(S) : Kie Y. Ahn and Leonard Forbes

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Title page item 56
Pg. 2, col. 1, U.S. PATENT DOCUMENTS –
Please insert the following patents:

--6,013,553	*	1/2000	Wallace et al.
6,348,373	*	2/2002	Ma et al.
6,407,435		6/2002	Ma et al.
6,495,474		12/2002	Rafferty et al.
6,573,160		6/2003	Taylor et al.
6,632,729	*	10/2003	Paton
6,679,996	*	1/2004	Yao
6,713,846		3/2004	Senzaki
6,784,508	*	8/2004	Tsunashima et al.
2002/0190302		12/2002	Bojarczuk et al.--

Col. 2, line 24 –
Replace "additional requirements. Thus it would desirable provide"
With --additional requirements. Thus it would be desirable to provide--

Col. 5, line 37 –
Replace "evaporative processes and in particular an electron beam"
With --evaporative process and in particular an electron beam--

Col. 6, line 7 –
Replace "by using a physical deposition (PVD) method as previously"
With --by using a physical vapor deposition (PVD) method as previously--

Col. 7, line 67 –
Replace "oxidation conditions only one effective method and that"
With --oxidation conditions represent only one effective method and that--

Col. 9, line 13 –
Replace "will be understood that the selection of Hf and La form the"
With --will be understood that the selection of Hf and La to form the--

Col. 9, line 36, claim **1** –
Replace "the second layer to temperature effective to form a first"
With --the second layer to a temperature effective to form a first--

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Col. 9, line 61, claim **8** –
Replace "heating to a temperature from about 200° C. to about 400 C."
With --heating to a temperature from about 200° C. to about 400° C.--

Col. 10, line 42, claim **17** –
Replace "heating the metal lever and layer of silicon dioxide to a"
With --heating the metal layer and layer of silicon dioxide to a--

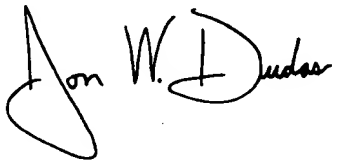
Col. 10, line 47, claim **17** –
Replace "dielectric lever over the surface, all the metal of the first"
With --dielectric layer over the surface, all the metal of the first--

Col. 11, line 17, claim **22** –
Replace "heating to a temperature from about 200° C. to about 200°"
With --heating to a temperature from about 200° C. to about 400°--

Col. 12, lines 15-16, claim **23** –
Replace "the raction chamber and heating the hafnium-containing"
With --the reaction chamber and heating the hafnium-containing--

Signed and Sealed this

Twenty-fifth Day of November, 2008



JON W. DUDAS
Director of the United States Patent and Trademark Office